

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L^2 - π -MOSV)**2SK2789**

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 66m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 16S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 100V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0V$ ($V_{DS} = 10V$, $I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	27	A
	Pulse	I_{DP}	108	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	60	W
Single Pulse Avalanche Energy**		E_{AS}	193	mJ
Avalanche Current		I_{AR}	27	A
Repetitive Avalanche Energy*		E_{AR}	6	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.08	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C/W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

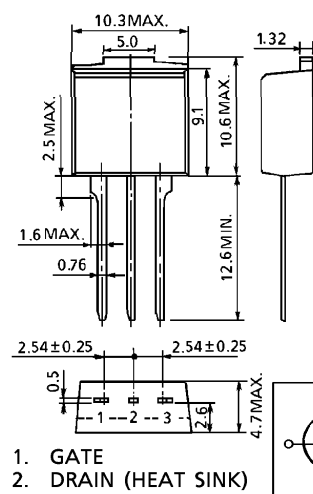
** $V_{DD} = 25V$, Starting $T_{ch} = 25^\circ C$, $L = 428\mu H$
 $I_{AR} = 27A$, $R_G = 25\Omega$

This transistor is an electrostatic sensitive device.
Please handle with caution.

INDUSTRIAL APPLICATIONS

TO-220FL

Unit in mm



JEDEC

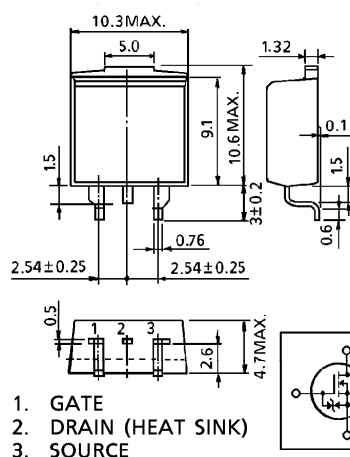
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EIAJ

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TOSHIBA 2-10S1B

TO-220SM



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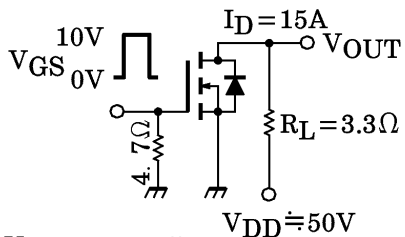
TOSHIBA 2-10S2B

Weight : 1.5g

961001EAA2

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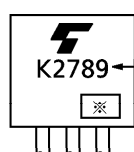
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	100	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4V, I_D = 15A$	—	0.09	0.13	Ω
			$V_{GS} = 10V, I_D = 15A$	—	0.066	0.085	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 15A$	8	16	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$	—	1100	—	pF
Reverse Transfer Capacitance		C_{rss}		—	180	—	
Output Capacitance		C_{oss}		—	400	—	
Switching Time	Rise Time	t_r		—	20	—	ns
	Turn-on Time	t_{on}		—	30	—	
	Fall Time	t_f		—	50	—	
	Turn-off Time	t_{off}		—	140	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = 80V, V_{GS} = 10V, I_D = 27V$	—	50	—	nC
Gate-Source Charge		Q_{gs}		—	34	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	16	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	27	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	108	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 27A, V_{GS} = 0V$	—	—	—1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 27A, V_{GS} = 0V$	—	155	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	0.31	—	μC

MARKING



TYPE

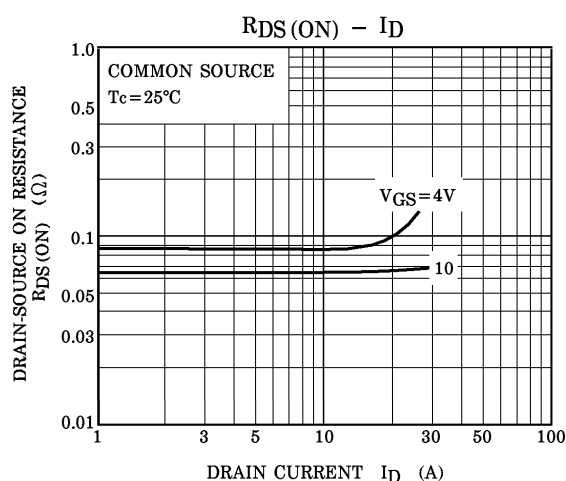
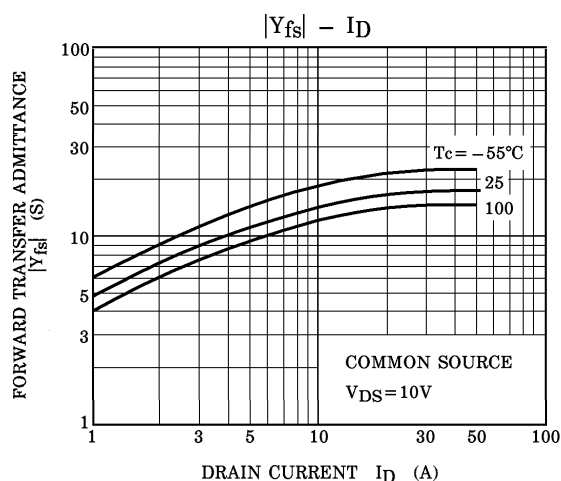
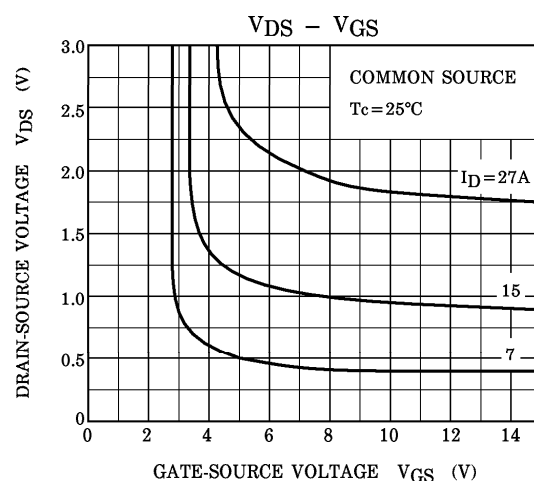
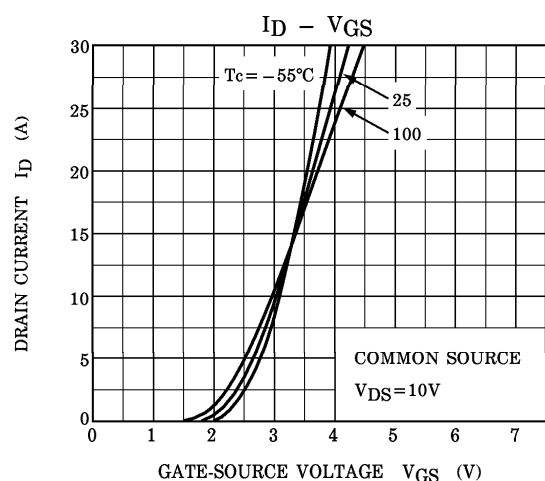
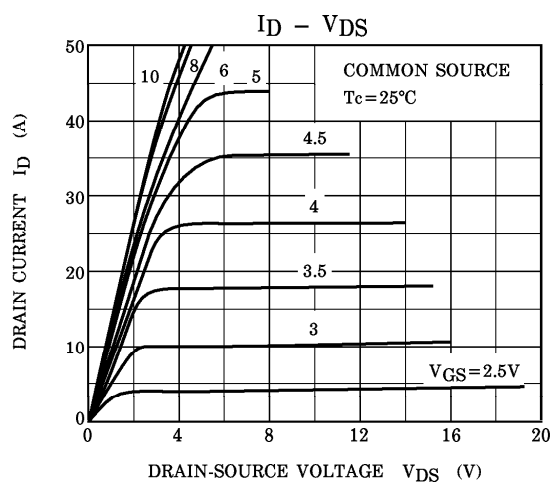
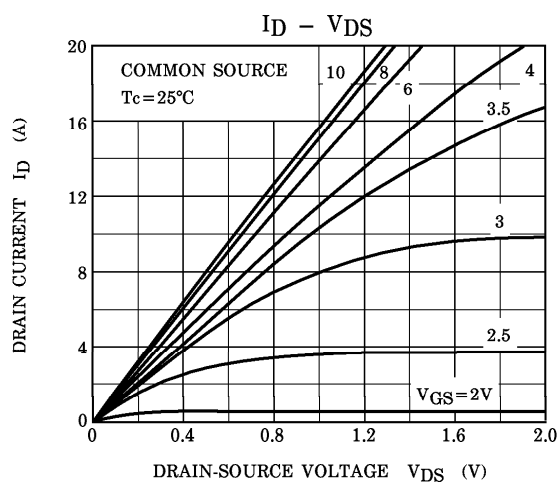
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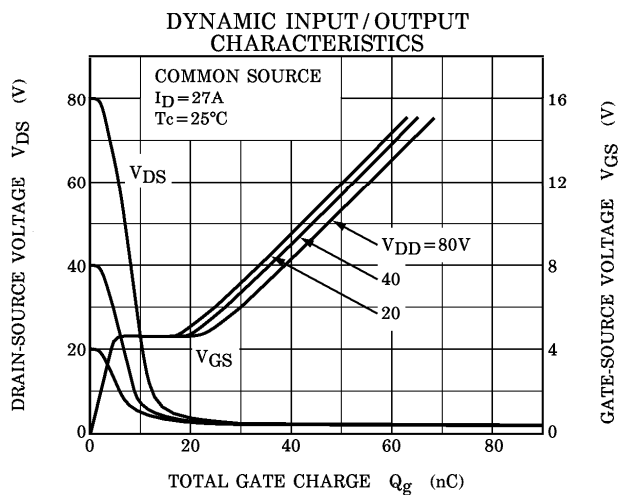
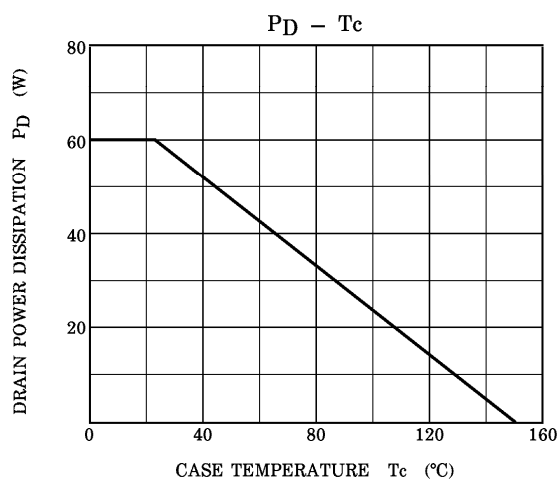
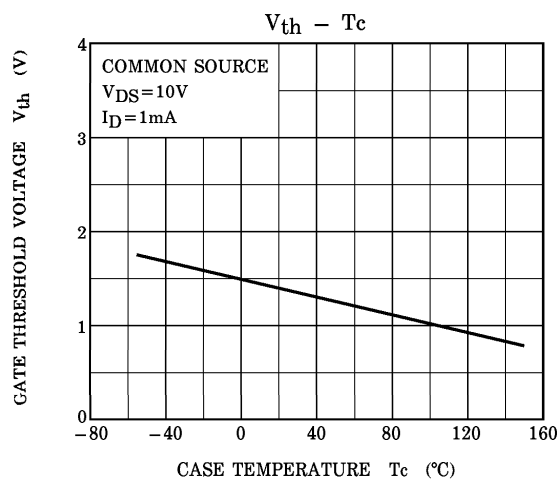
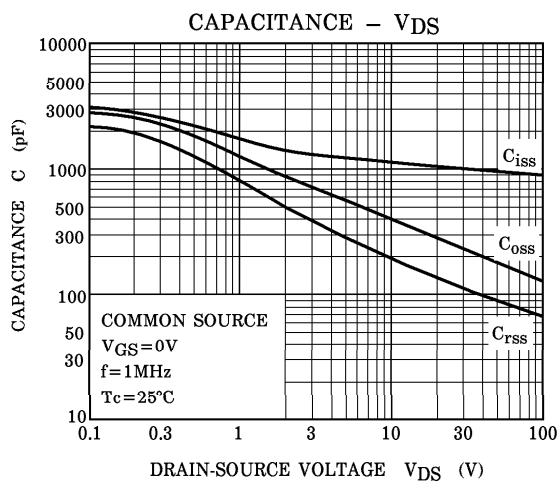
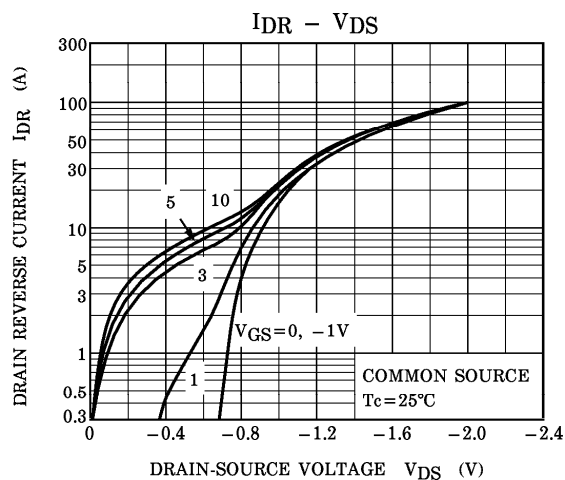
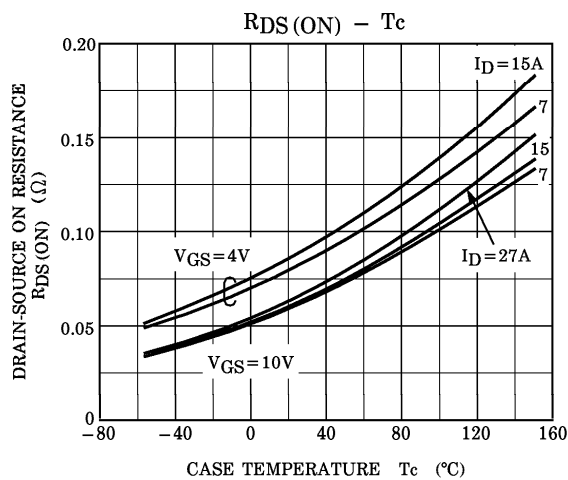


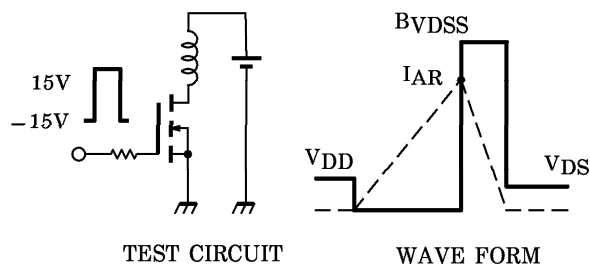
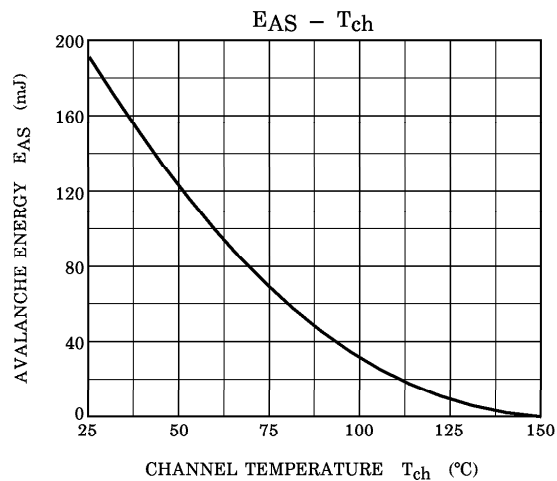
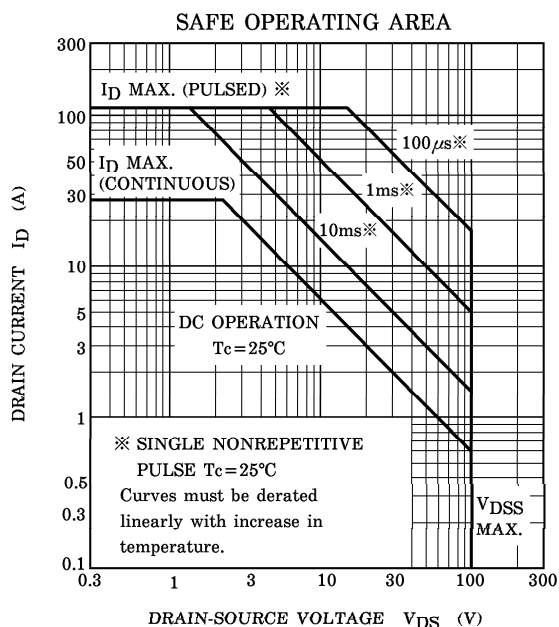
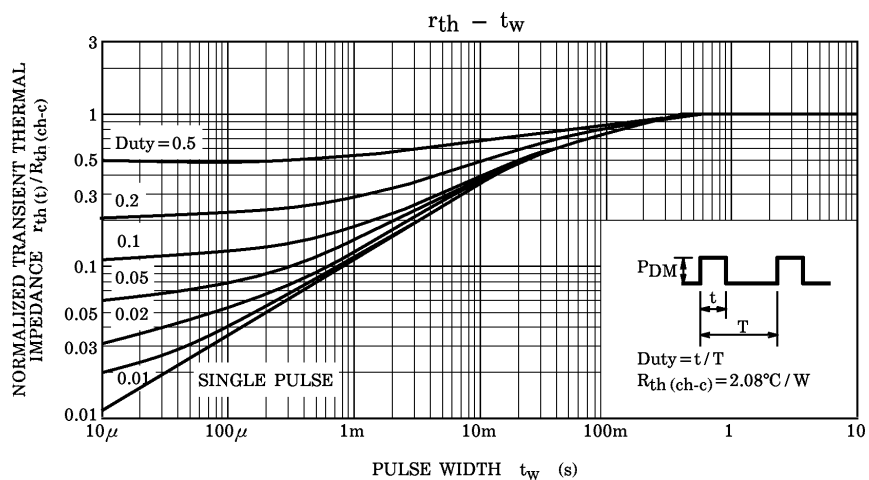
Month (Starting from Alphabet A)



Year (Last Number of the Christian Era)







Peak $I_{AR} = 27A$, $R_G = 25\Omega$
 $V_{DD} = 25V$, $L = 428\mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$